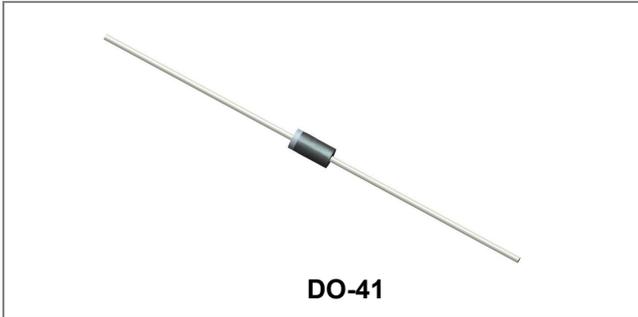


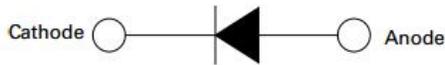
**1N4001G THRU 1N4007G
1.0A GLASS PASSIVATED RECTIFIER**



Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- This is a Pb – Free Device
- “-HF” suffix is for Halogen Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: molded plastic
- Terminals: Plated leads, solderable per MIL-STD-202, Method 208
- Polarity: Cathode band
- Mounting Position: Any
- Weight: 0.34 grams (approx)

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

| Type Number | Symbol | 1N 4001G | 1N 4002G | 1N 4003G | 1N 4004G | 1N 4005G | 1N 4006G | 1N 4007G | Units |
|---|------------------|-------------|----------|----------|----------|----------|----------|----------|-------|
| Peak Repetitive Reverse Voltage | V _{RRM} | | | | | | | | V |
| Working Peak Reverse Voltage | V _{RWM} | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| DC Blocking Voltage | V _R | | | | | | | | V |
| RMS Reverse Voltage | V _{RMS} | 35 | 70 | 140 | 280 | 420 | 560 | 700 | V |
| Average forward rectified output current @T _A = 75°C | I _O | 1.0 | | | | | | | A |
| Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method) | I _{FSM} | 30 | | | | | | | A |
| Forward Voltage @I _F = 1.0A | V _{FM} | 1.0 | | | | | | | V |
| Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C | I _{RM} | 5.0 50 | | | | | | | μA |
| Typical Junction Capacitance (Note 2) | C _J | 8 | | | | | | | pF |
| Typical Thermal Resistance Junction to Ambient (Note 1) | R _{θJA} | 100 | | | | | | | °C/W |
| Operating Junction Temperature Range | T _J | -65 to +175 | | | | | | | °C |
| Storage Temperature Range | T _{STG} | -65 to +175 | | | | | | | °C |

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

Ratings and Characteristics Curves

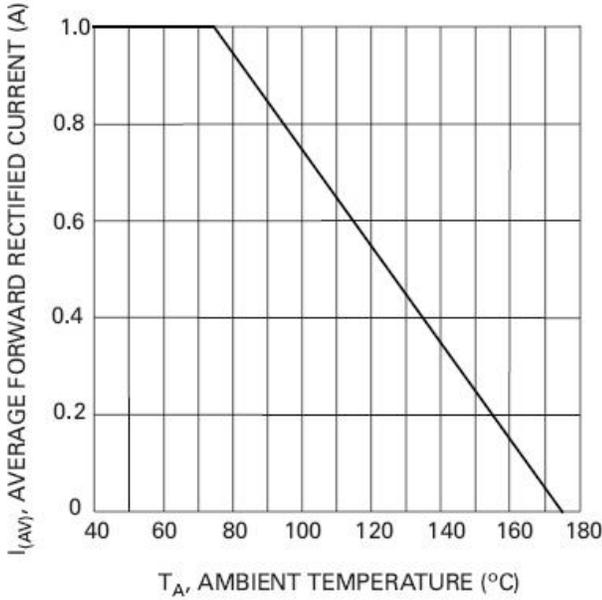


Fig. 1 Forward Current Derating Curve

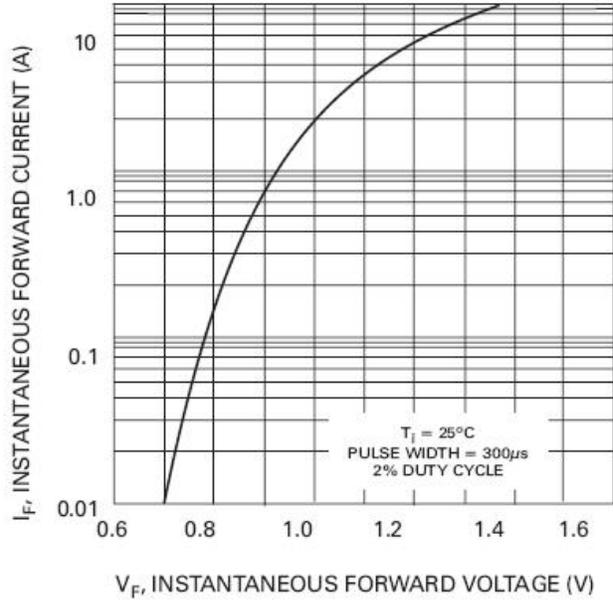


Fig. 2 Typical Forward Characteristics

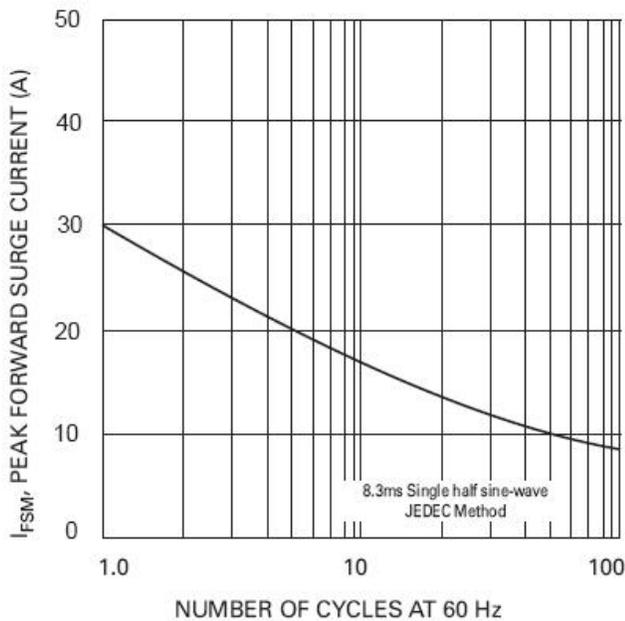


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

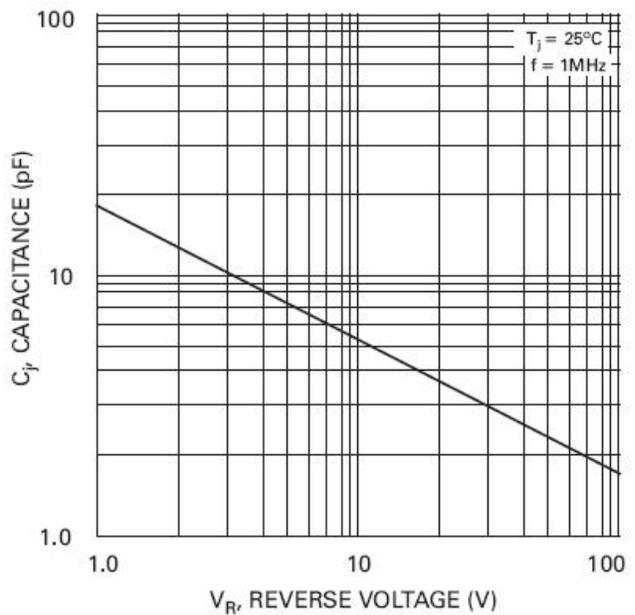
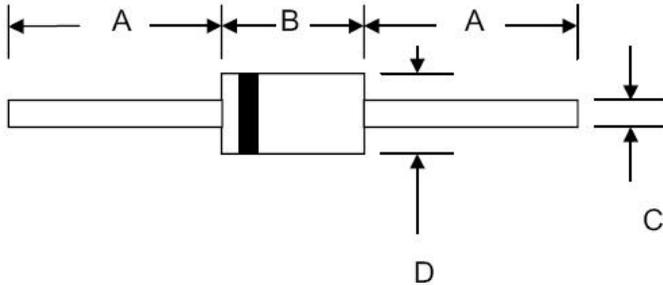


Fig. 4 Typical Junction Capacitance

Mechanical Dimensions DO-41



| SYMBOL | Millimeters | | Inches | |
|--------|-------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 25.4 | - | 1.000 | - |
| B | 4.06 | 5.21 | 0.160 | 0.205 |
| C | 0.71 | 0.864 | 0.028 | 0.034 |
| D | 2.00 | 2.72 | 0.079 | 0.107 |

Ordering Information

| Device | Package | Shipping |
|-------------------------|--------------------|----------------|
| 1N4001G-1N4007G | DO-41 (Pb-Free) | 5000pcs / Tape |
| 1N4001GTA- 1N4007GTA | DO-41 (Pb-Free) | 5000pcs / Tape |

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



1N4001G

Where XXXXX is YYWWL

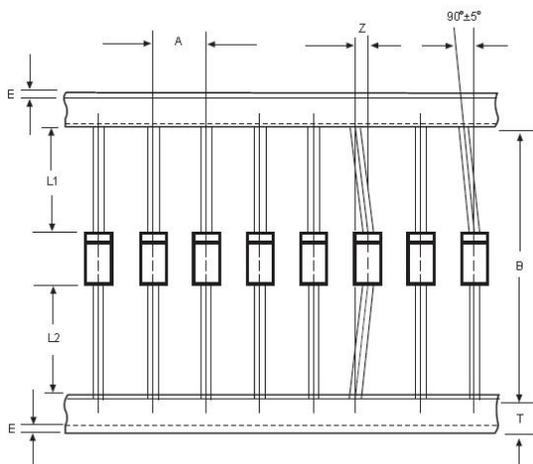
1N4001G = Type Number
SSG = SSG
HF = Halogen Free
YY = Year
WW = Week
L = Lot Number



1N4001G-HF

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification DO-41



| SYMBOL | Millimeters | |
|---------|-------------|------|
| | Min. | Max. |
| A | 4.50 | 5.50 |
| B | 50.9 | 53.9 |
| Z | - | 1.20 |
| T | 5.60 | 6.40 |
| E | - | 0.80 |
| IL1-L2I | - | 1.0 |

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